

Amendments to the specification

Please make the following amendments to the specification:

On page 4, lines ²²~~23~~-25, please make the following amendment

mp 6/9/08

[0030] According to still a further feature of the method of the invention, the first and second pattern layers are layers of polycrystalline silicon or metal, or nitride, or silicon, or silica, or [[HiK]] High-K material.

On page 6, lines ²⁰~~22~~-26, please make the following amendment

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The first pattern layer 5 has chemical etching selectivity relatively to silicon oxide. As this will appear subsequently, layer 5 is a layer in which the first pattern is formed. Generally, the first pattern layer 5 may for example be a layer of polycrystalline silicon, of metal, of silicon nitride (Si_3N_4), a High-K (also known as High-K dielectric) material or of gate insulator topped with a stack of gate layers.